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U.S. PATENT DOCUMENTS

Examiner Initial		Document Number							Date	Name	Class	Subclass	Filing Date if Appropriate
<i>MA</i>	AA	5	8	6	8	8	3	7	February 9, 1999	DiSalvo et al.			
	AB												
	AC												
	AD												

FOREIGN PATENT DOCUMENTS

		Document Number							Date	Country	Class	Subclass	Translation	
													Yes No	
<i>MA</i>	AL	102	5	6	6	6	6	2	September 25, 1998	Japan				ABST.
<i>MA</i>	AM	2000	32	7	4	9	5		November 28, 2000	Japan				ABST.
<i>MA</i>	AN	2000	2	2	2	1	2		January 21, 2000	Japan				ABST.
<i>MA</i>	AO	2000	1	2	9	0	0		January 14, 2000	Japan				ABST.

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

<i>MA</i>	AP	Shuji NAKAMURA et al. "InGaN/GaN/AlGaN-Based Laser Diodes with Modulation-Doped Strained-Layer Superlattices", pp. L1568-L1571.
<i>MA</i>	AQ	Shuji NAKAMURA et al. "InGaN/GaN/AlGaN-Based Laser Diodes with Laser Diodes with Cleaved Facets Grown on GaN Substrates", pp. 832-834.
<i>MA</i>	AR	Sylwester POROWSKI, "Bulk and Homoepitaxial GaN-growth and Characterisation", pp. 153-158.
<i>MA</i>	AS	Hisanori YAMANE et al. "Preparation of GaN Single Crystal Using a Na Flux", pp. 413-416.
<i>MA</i>	AS	Appln. Serial No. 09/590,063 filed June 8, 2000

EXAMINER	DATE CONSIDERED
<i>MA</i>	7/14/03

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609: Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.